

International IOR Rectifier

SMPS MOSFET

IRF5802PbF

HEXFET® Power MOSFET

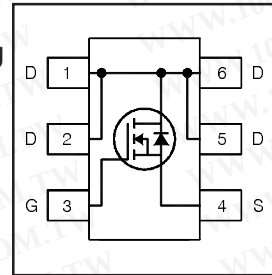
Applications

- High frequency DC-DC converters

Benefits

- Low Gate to Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current
- Lead-Free
- Halogen-Free

V_{DSS}	$R_{DS(on)}$ max	I_D
150V	$1.2\Omega @ V_{GS} = 10V$	0.9A



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	0.9	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	0.7	
I_{DM}	Pulsed Drain Current ①	7.0	
$P_D @ T_A = 25^\circ C$	Power Dissipation②	2.0	W
	Linear Derating Factor	0.02	W/°C
V_{GS}	Gate-to-Source Voltage	± 30	V
dv/dt	Peak Diode Recovery dv/dt ③	7.1	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient④	62.5	°C/W

Notes ① through ⑥ are on page 8

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	150	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.19	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$ ③
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	1.2	Ω	$V_{GS} = 10V, I_D = 0.54A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 150V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 120V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 30V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -30V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	0.55	—	—	S	$V_{DS} = 50V, I_D = 0.54A$
Q_g	Total Gate Charge	—	4.5	6.8	nC	$I_D = 0.54A$
Q_{gs}	Gate-to-Source Charge	—	1.0	1.5		$V_{DS} = 120V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.4	3.6		$V_{GS} = 10V,$
$t_{d(on)}$	Turn-On Delay Time	—	6.0	—	ns	$V_{DD} = 75V$
t_r	Rise Time	—	1.6	—		$I_D = 0.54A$
$t_{d(off)}$	Turn-Off Delay Time	—	7.5	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	9.2	—		$V_{GS} = 10V$ ③
C_{iss}	Input Capacitance	—	88	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	26	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	7.7	—		$f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	110	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	14	—		$V_{GS} = 0V, V_{DS} = 120V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	3.0	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 120V$ ③

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy②	—	9.5	mJ
I_{AR}	Avalanche Current①	—	0.9	A

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.8	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	18		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 0.54A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	46	69	ns	$T_J = 25^\circ\text{C}, I_F = 0.54A$
Q_{rr}	Reverse Recovery Charge	—	55	83	nC	$di/dt = 100A/\mu s$ ③

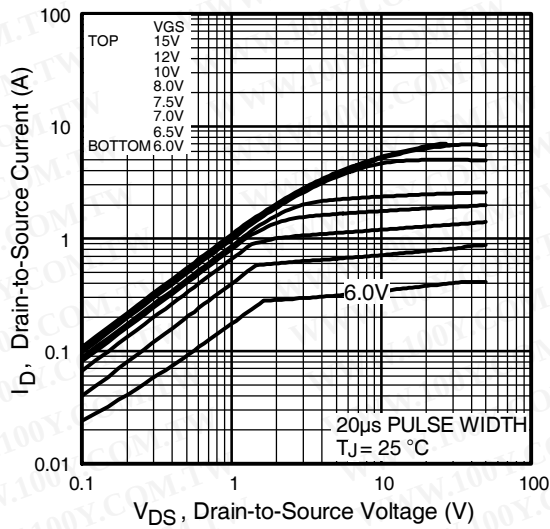


Fig 1. Typical Output Characteristics

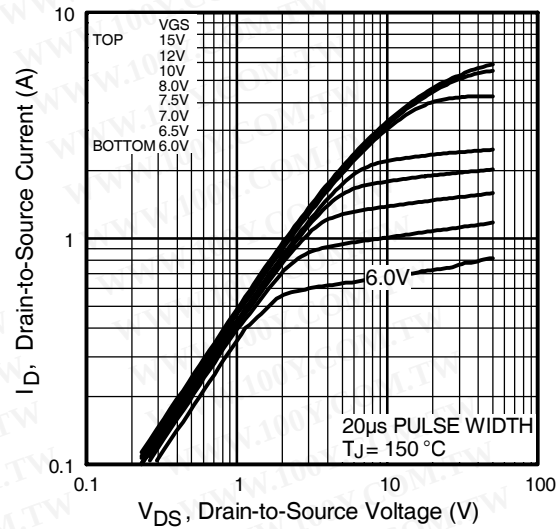


Fig 2. Typical Output Characteristics

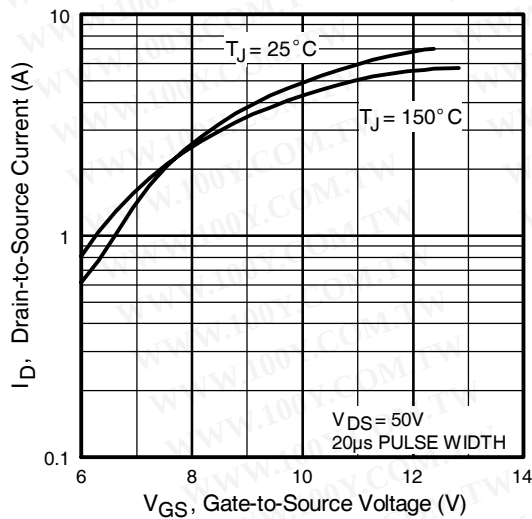


Fig 3. Typical Transfer Characteristics

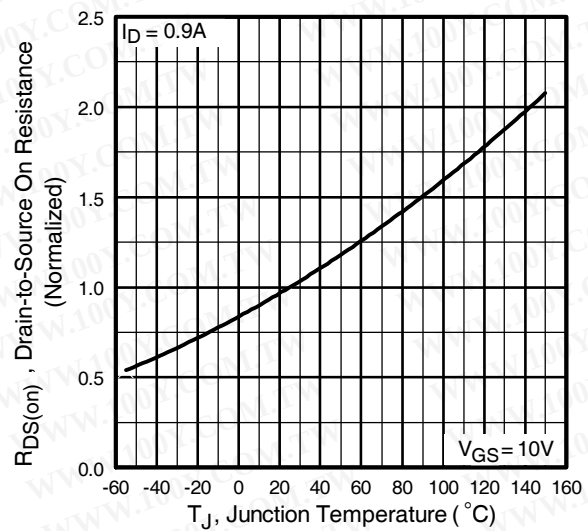
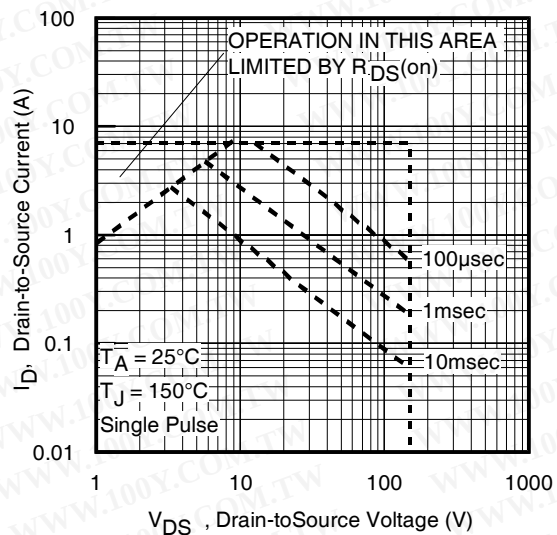
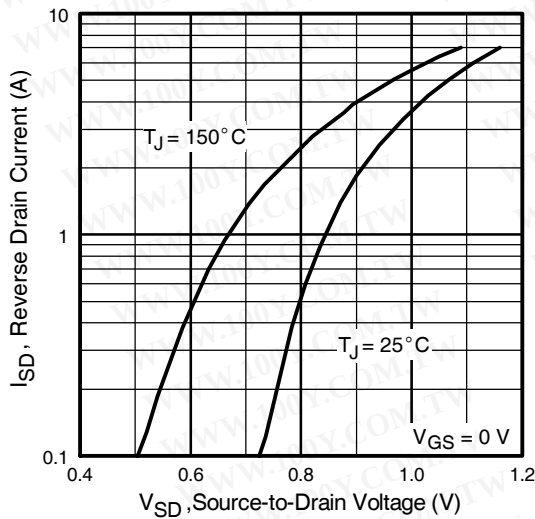
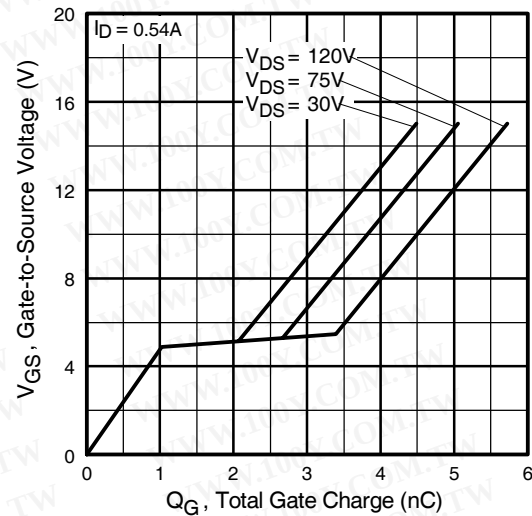
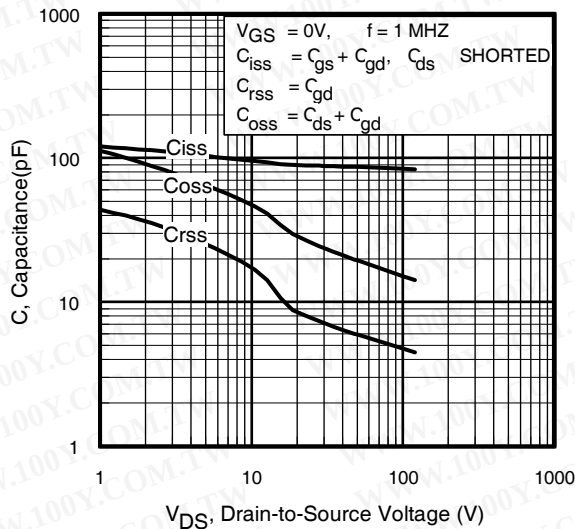


Fig 4. Normalized On-Resistance
Vs. Temperature

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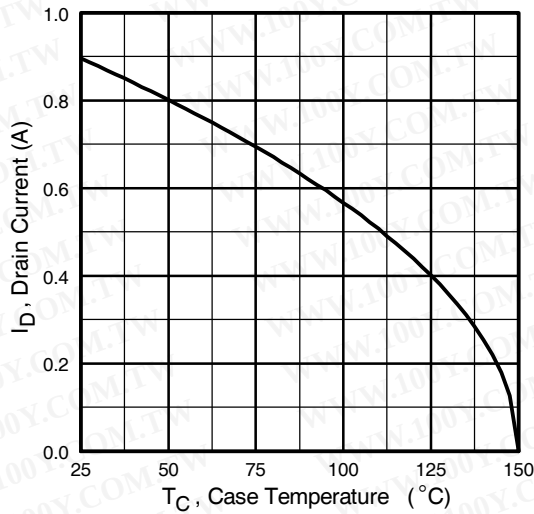


Fig 9. Maximum Drain Current Vs. Case Temperature

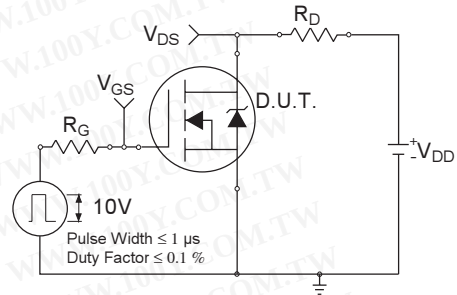


Fig 10a. Switching Time Test Circuit

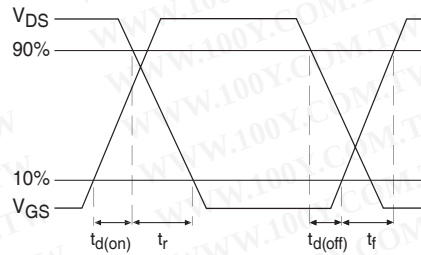


Fig 10b. Switching Time Waveforms

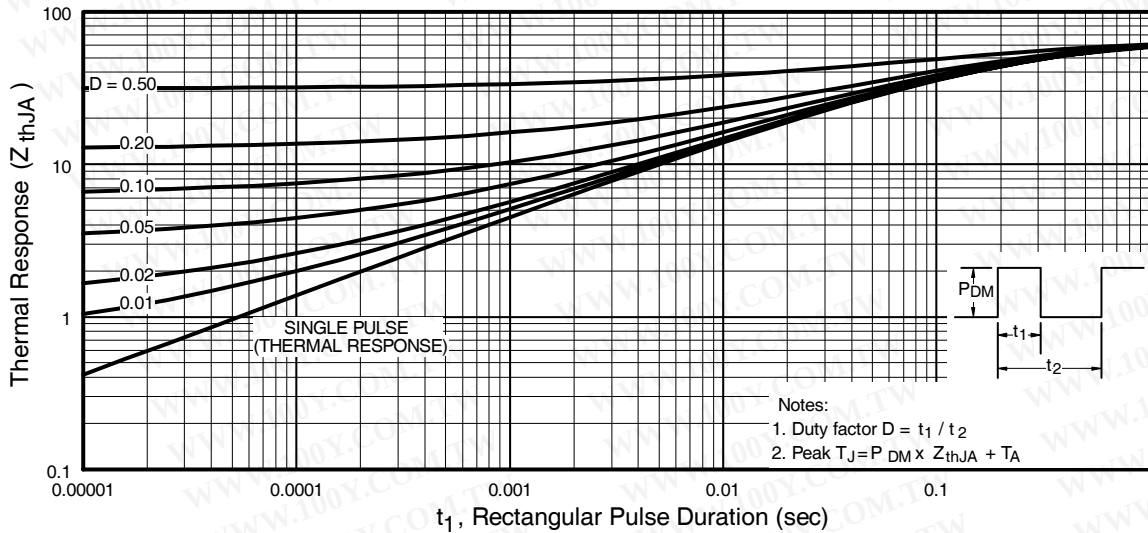


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

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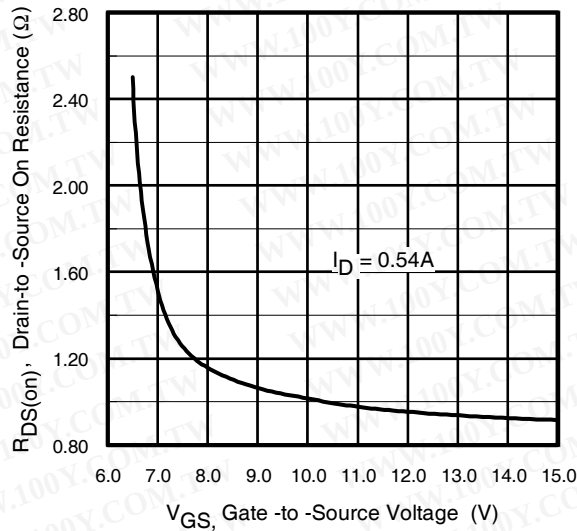


Fig 12. Typical On-Resistance Vs. Gate Voltage

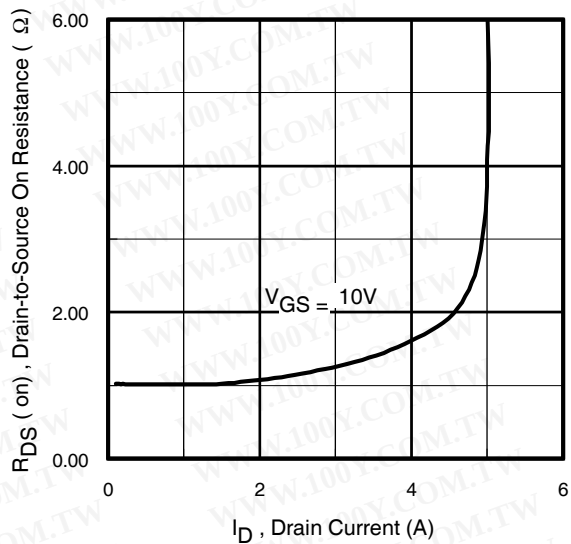


Fig 13. Typical On-Resistance Vs. Drain Current

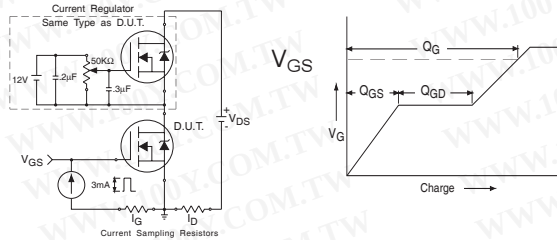


Fig 14a&b. Basic Gate Charge Test Circuit and Waveform

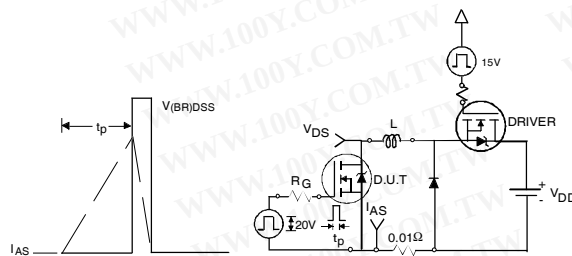


Fig 15a&b. Unclamped Inductive Test circuit and Waveforms

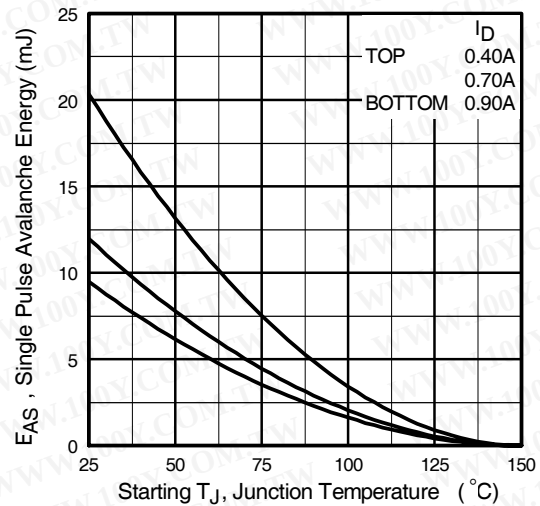
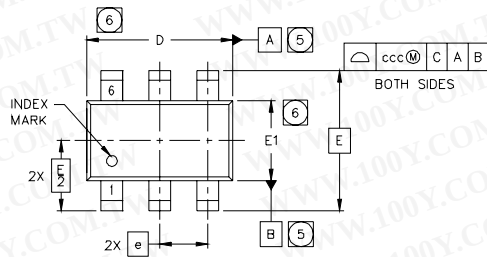


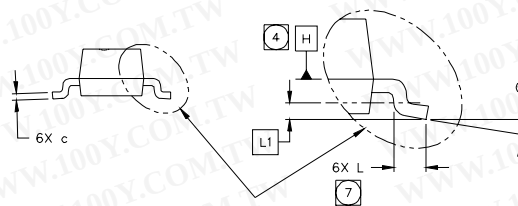
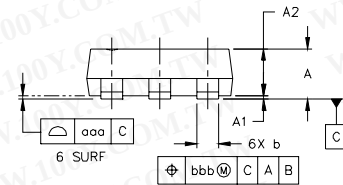
Fig 15c. Maximum Avalanche Energy Vs. Drain Current

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TSOP-6 Package Outline

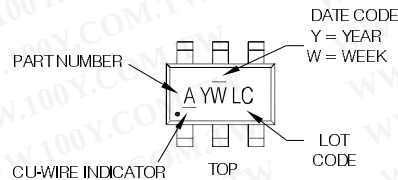


SYMBOL	MO-193AA DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	.0433
A1	0.01	---	0.10	.0004	---	.0039
A2	0.80	0.90	1.00	.0315	.0354	.0393
b	0.25	---	0.50	.0099	---	.0196
c	0.10	---	0.26	.004	---	.010
D	2.90	3.00	3.10	.115	.118	.122
E	2.75 BSC			.108 BSC		
E1	1.30	1.50	1.70	.052	.059	.066
e	1.00 BSC			.039 BSC		
L	0.20	0.40	0.60	.0079	.0157	.0236
L1	0.30 BSC			.0118 BSC		
Ø	0"	---	8"	0"	---	8"
aaa	0.10			.004		
bbb	0.15			.006		
ccc	0.25			.010		



TSOP-6 Part Marking Information

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

A = SI3443DV K = IRF5810
B = IRF5800 L = IRF5804
C = IRF5850 M = IRF5803
D = IRF5851 N = IRF5802
E = IRF5852
F = IRF5801
I = IRF5805
J = IRF5806

Notes:

- A line above the work week (as shown here) indicates Lead-Free
- A line below the part number (as shown here) indicates Cu-wire

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

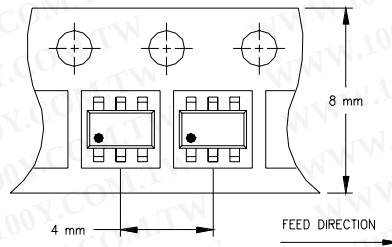
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TSOP-6 Tape & Reel Information

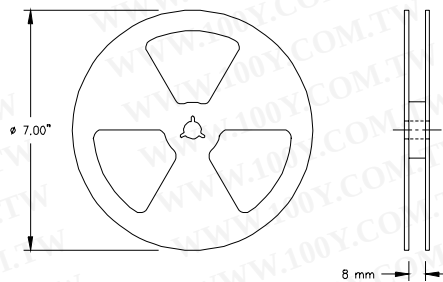
勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

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NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES:

1. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 23\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 0.54\text{A}$.
- ③ Pulse width $\leq 400\mu\text{s}$; duty cycle $\leq 2\%$.
- ④ When mounted on 1 inch square copper board
- ⑤ C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 80% V_{DSS}
- ⑥ $I_{SD} \leq 0.54\text{A}$, $di/dt \leq 89\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

Data and specifications subject to change without notice.

This product has been designed and qualified for the Consumer market.

Qualification Standards can be found on IR's Web site.

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